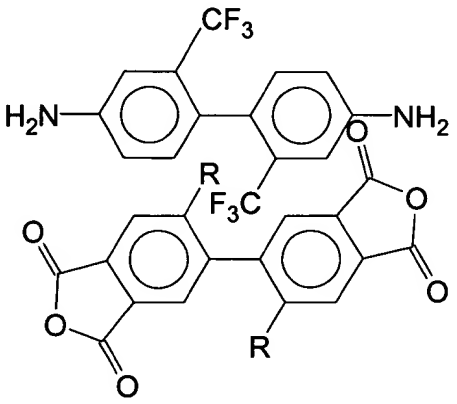
LISTING OF THE CLAIMS

1. (previously presented) An insulated integrated circuit comprising:

An integrated circuit; and

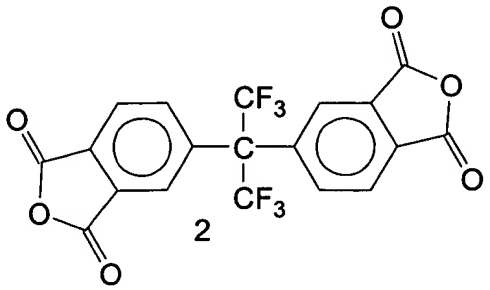
An insulating layer having a dielectric constant of less than about 2. 5 is disposed on said integrated circuit, wherein said insulating layer is a polyimide film that is the polymerization product of polymerization product of an aromatic diamine having the general formula (I):

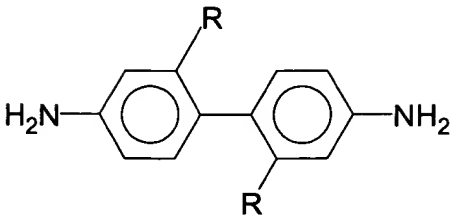


and an aromatic dianhydride having the formula (II):

wherein R is an organic substituent selected from the group consisting of CF_3, o-trifluoromethyl phenyl, m-trifluoromethyl phenyl, p-trifluoromethyl phenyl and 3,5 bis[(m-trifluoromethyl) phenyl]; or

the polymerization product of an ormatic dianhydride having the general formula (III):





and an aromatic diamine having the formula (IV):

wherein R is a substituent selected from the group consisting of trifluoromethyl, o-trifluoromethyl phenyl, m-trifluoromethyl phenyl, p-trifluoromethyl phenyl and 3,5'-bis[(m-trifluoromethyl) phenyl];

further wherein the dielectric constant of said insulating layer is less than about 2. 5.

2. (original) The insulated integrated circuit according to claim 1, wherein said integrated circuit is a microprocessor.

3. (original) The insulated integrated circuit according to claim 1, wherein the thickness of said insulating layer is from about 10 to about 1000 microns.

4. (original) The insulated integrated circuit according to claim 1, wherein the thickness of said insulating layer is from about 10 to about 500 microns.

5. (original) The insulated integrated circuit according to claim 1, wherein the thickness of said insulating layer is from about 10 to about 100 microns.

6. (canceled)

7. (canceled)

8. (canceled)

9. (original) The insulated integrated circuit according to claim 1, wherein the coefficient of thermal expansion is greater than about $23x10^{-6/o}C$.

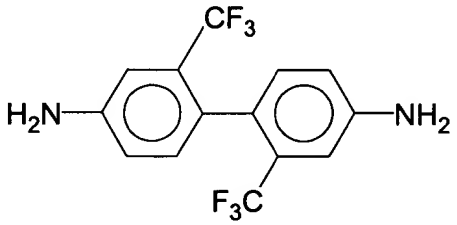
10. (original) The insulated integrated circuit according to claim 1, wherein the coefficient of thermal expansion is greater than about $42x10^{-6/o}C$.

11. (original) The insulated integrated circuit according to claim 1, wherein the coefficient of thermal expansion is greater than about $50x10^{-6/o}C$.

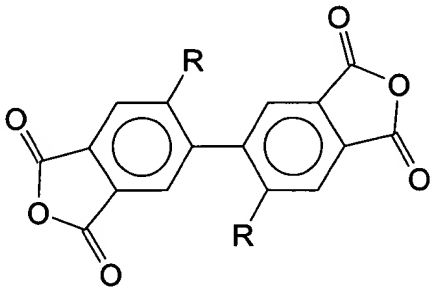
12. (previously presented) An insulated electrically conductive component comprising:

an electrically conductive component; and

an insulating layer comprising the polylmerization product of an aromatic diamine having the general formula (I):



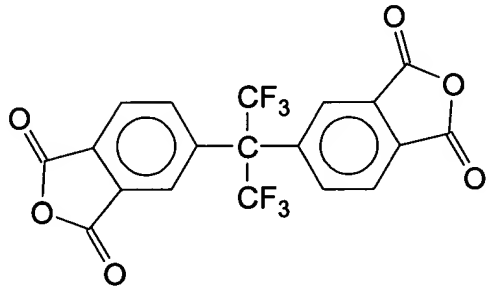
and an aromatic dianhydride having the formula (II):



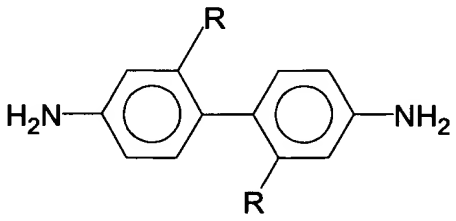
wherein R is an organic substituent selected from the group consisting of CF_3, o-trifluoromethyl phenyl, m-trifluoromethyl phenyl, p-trifluoromethyl phenyl and 3,5-bis[(m-

trifluoromethyl) phenyl]; or

the polymerization product of an aromatic dianhydride having the general formula (III):



and an aromatic diamine having the formula (IV):



wherein R is a substituent selected from the group consisting of trifluoromethyl, o-trifluoromethyl phenyl, m-trifluoromethyl phenyl, p-trifluoromethyl phenyl and 3,5'-bis[(m-trifluoromethyl) phenyl],_wherein

the coefficient of thermal expansion of the insulated electrically conductive component is greater than about $23x10^{-6/o}C$.

13. (previously presented) The insulated electrically conductive component according to claim 12, wherein said electrically conductive component is selected from the group consisting of capacitors, diodes, connectors and transistors.

14. (original) The insulated electrically conductive component according to claim 12, wherein the thickness of said insulating layer is from about 10 to about 1000 microns.

15. (original) The insulated electrically conductive component according to claim 12, wherein the thickness of said insulating layer is from about 10 to about 500 microns.

16. (original) The insulated electrically conductive component according to claim 12, wherein the thickness of said insulating layer is from about 10 to about 100 microns.

17. (original) The insulated electrically conductive component according to claim 12, wherein the dielectric constant of said insulating layer is less than about 2.8.

18. (original) The insulated electrically conductive component according to claim 12, wherein the dielectric constant of said insulating layer is less than about 2.7.

19. (original) The insulated electrically conductive component according to claim 12, wherein the dielectric constant of said insulating layer is less than about 2.5.

20. (canceled)

21. (original) The insulated electrically conductive component according to claim 12, wherein the coefficient of thermal expansion is greater than about $42x10^{-6/o}C$.

22. (original) The insulated electrically conductive component according to claim 1, wherein the coefficient of thermal expansion is greater than about $50x10^{-6/o}C$.

23. (canceled)

24. (canceled)

25. (canceled)